PROCEEDINGS OF SPIE

Photomask and Next-Generation Lithography Mask Technology XVI

Kunihiro Hosono
Editor

8–10 April 2009
Yokohama, Japan

Sponsored by
PMJ Photomask Japan
BACUS
SPIE

Published by
SPIE

Volume 7379

Proceedings of SPIE, 0277-786X, v. 7379

SPIE is an international society advancing an interdisciplinary approach to the science and application of light.

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Please use the following format to cite material from this book:
Author(s), "Title of Paper," in *Photomask and Next-Generation Lithography Mask Technology XVI*, edited by Kunihiro Hosono, Proceedings of SPIE Vol. 7379 (SPIE, Bellingham, WA, 2009) Article CID Number.

ISSN 0277-786X
ISBN 9780819476562

Published by
SPIE
P.O. Box 10, Bellingham, Washington 98227-0010 USA
Telephone +1 360 676 3290 (Pacific Time) · Fax +1 360 647 1445
SPIE.org

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Printed in the United States of America.

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Contents

xiii *Symposium Committees*
xv *Conference Committees*

INVITED SESSION

7379 02 **Litho/mask strategies for 32-nm half-pitch and beyond: using established and adventurous tools/technologies to improve cost and imaging performance (Keynote Paper)** [7379-01]
B. J. Lin, Taiwan Semiconductor Manufacturing Co. Ltd. (Taiwan)

MATERIAL AND PROCESS I

7379 06 **The novel plasma etching process for defect reduction in photomask fabrication** [7379-05]
J.-H. Lee, I.-Y. Jang, Y. S. Jeong, B. Seung, S.-Y. Moon, S.-G. Woo, H. K. Cho, SAMSUNG Electronics Co., Ltd. (Korea, Republic of)

7379 07 **Etch characterization of binary mask dependence on mask material and resist thickness for 22nm mask fabrication** [7379-06]
S. Nemoto, Toppan Photomasks, Inc. (United States); T. Faure, R. Wistrom, S. Crawford, G. Reid, P. Bartlau, IBM Corp. (United States); T. Komizo, Toppan Photomasks, Inc. (United States); A. E. Zweber, IBM Corp. (United States)

MATERIAL AND PROCESS II

7379 09 **Effect of pellicle frame and adhesive material on final photomask flatness** [7379-08]
N. Zhou, K. Racette, D. Hasselbeck, M. Barrett, R. Nolan, M. Caterer, IBM Corp. (United States); T. Mizoguchi, S. Akutagawa, Toppan Photomasks, Inc. (Japan); G. Dickey, T. Shirasaki, ShinEtsu Chemical Co. Ltd. (Japan)

7379 0A **Adhesion control between resist patterns and photomask blank surfaces** [7379-09]
M. Kurihara, Dai Nippon Printing Co., Ltd. (Japan) and Tokyo Institute of Technology (Japan); S. Hatakeyama, K. Yoshida, T. Nagai, D. Totsukawa, M. Fukuda, Y. Morikawa, H. Mohri, M. Hoga, N. Hayashi, Dai Nippon Printing Co., Ltd. (Japan); H. Ohtani, M. Fujihira, Tokyo Institute of Technology (Japan)

7379 0B **Investigation of the development process for high-precision patterning** [7379-10]
J. Watanabe, T. Yamazaki, M. Tanabe, Toppan Printing Co., Ltd. (Japan); T. Komizo, Toppan Photomasks Inc. (United States); A. E. Zweber, A. C. Smith, IBM Corp. (United States)

7379 0D **Study on surface integrity in photomask resist strip and final cleaning processes** [7379-12]
S. Singh, Hamatech USA Inc. (United States); S. Helbig, P. Dress, HamaTech APE (Germany); U. Dietze, Hamatech USA Inc. (United States)

7379 0F **Haze growth on reticles: What's the RigHT thing to do?** [7379-14]
S. M. McDonald, D. V. Chalom, M. J. Green, J. A. McMurran, Photronics, Inc. (United States); M. B. Garrett, Micron Technology, Inc. (United States); D. W. Dlouhy, Photronics, Inc. (United States)

EUVL MASK I

7379 0G **SEMATECH EUVL mask program status (Invited Paper)** [7379-15]
H. Yun, F. Goodwin, S. Huh, K. Orvek, B. Cha, A. Rastegar, P. Kearney, SEMATECH, Inc. (United States)

7379 0H **Actinic EUVL mask blank inspection and phase defect characterization** [7379-16]
T. Yamane, T. Iwasaki, T. Tanaka, T. Terasawa, O. Suga, Semiconductor Leading Edge Technologies, Inc. (Japan); T. Tomie, National Institute of Advanced Industrial Science and Technology (Japan)

7379 0I **Improvement of EUVL mask blank inspection capability at Intel** [7379-17]
A. Ma, T. Liang, S.-J. Park, G. Zhang, Intel Corp. (United States); T. Tamura, K. Omata, Y. Sato, H. Kusunose, Lasertec Corp. (Japan)

7379 0J **Thorough characterization of an EUV mask** [7379-18]
H. Mizuno, Toshiba America Electronic Components, Inc. (United States); G. McIntyre, C. Koay, IBM Advanced Lithography research (Univted States); M. Burkhardt, IBM Corp. (United States); L. He, SEMATECH, Inc. (United States); J. Hartley, C. Johnson, S. Raghunathan, College of Nanoscale Science and Engineering (United States); K. Goldberg, I. Mochi, Lawrence Berkeley National Lab. (United States); B. La Fontaine, O. Wood, GLOBALFOUNDARIES (United States)

NIL AND PATTERNED MEDIA

7379 0K **Nano-pattern design and technology for patterned media magnetic recording (Invited Paper)** [7379-19]
H. Kataoka, Hitachi Global Storage Technologies Japan, Ltd. (Japan); Y. Hirayama, Hitachi, Ltd. (United States); T. R. Albrecht, M. Kobayashi, Hitachi Global Storage Technologies, Inc. (United States)

7379 0L **Si-mold fabrication for patterned media using high-resolution chemically amplified resist** [7379-20]
M. Fukuda, T. Chiba, M. Ishikawa, K. Itoh, M. Kurihara, M. Hoga, Dai Nippon Printing Co., Ltd. (Japan)

7379 0M **Trade-off between inverse lithography mask complexity and lithographic performance** [7379-57]
B.-G. Kim, S. Suh, B.-S. Kim, S.-G. Woo, H.-K. Cho, SAMSUNG Electronics Co., Ltd. (Korea, Republic of); V. Tolani, G. Dai, D. Irby, K, Wang, G, Xiao, D. Kim, K.-H. Baik, B. Gleason, (Luminescent Technologies, Inc. (USA)

7379 0N **Inspection and repair for imprint lithography at 32 nm and below** [7379-22]
K. Selinidis, E. Thompson, S. V. Sreenivasan, D. J. Resnick, Molecular Imprints, Inc. (United States); M. Pritschow, J. Butschke, M. Irmscher, H. Sailer, Institut für Mikroelektronik Stuttgart (Germany); H. Dobberstein, NaWoTec GmbH, Carl Zeiss SMT Co. (Germany)

EUVL MASK II

7379 0O **Implications of image plane line-edge roughness requirements on extreme ultraviolet mask specifications (Invited Paper)** [7379-23]
P. P. Naulleau, S. A. George, Lawrence Berkeley National Lab. (United States)

7379 0P **Mask-induced aberration in EUV lithography** [7379-24]
Y. Nakajima, T. Sato, R. Inanami, T. Nakasugi, T. Higashiki, Toshiba Corp. (Japan)

7379 0Q **Evaluation of an e-beam correction strategy for compensation of EUVL mask non-flatness** [7379-25]
K. Orvek, J. Sohn, SEMATECH, Inc. (United States); J. Choi, SAMSUNG Electronics (United States); R. Engelstad, Univ. of Wisconsin, Madison (United States); S. Raghunathan, Univ. at Albany, SUNY (United States); J. Zimmerman, T. Laursen, ASML (United States); Y. Shusuke, NuFlare Technology, Inc. (United States); T. Shoki, HOYA Corp. (United States)

7379 0R **Investigation of EUV mask defectivity via full-field printing and inspection on wafer** [7379-26]
R. Jonckheere, D. Van Den Heuvel, F. Iwamoto, N. Stepanenko, A. Myers, M. Lamantia, A.-M. Goethals, E. Hendrickx, K. Ronse, IMEC (Belgium)

STRATEGY AND BUSINESS

7379 0T **Smart way to determine and guarantee mask specifications: trade-off between cost and quality (Invited Paper)** [7379-28]
F. Shigemitsu, Toshiba Corp., Semiconductor Co. (Japan)

7379 0U **Economics of automation for the design-to-mask interface** [7379-29]
W. Erck, Wes Erck & Associates (United States)

7379 0V **Novel mask qualification methodology with die-to-database wafer inspection system** [7379-30]
Y. Hagio, I. Nagahama, Y. Matsuoka, H. Mukai, K. Hashimoto, Toshiba Corp., Semiconductor Co. (Japan)

EDA, DFM, AND MDP

7379 0W **European MEDEA+ CRYSTAL project: DFM photomasks inputs for EDA workflow task force (Invited Paper)** [7379-31]
E. Beisser, XYALIS sarl (France); M. Tissier, Toppan Photomasks SAS (France); D. Au, Atmel Rousset SAS (France); S. Bonniol, Satin IP Technologies SAS (France); P. Garcia, Atmel Rousset SAS (France); P. Morey-Chaisemartin, XYALIS sarl (France); D. Sadran, Toppan Photomasks SAS (France); I. Servin, CEA, LETI (France); M. Tabusse, Satin IP Technologies SAS (France)

7379 0X **Reduction of MRC error review time through the simplified and classified MRC result** [7379-32]
C. W. Lee, J. C. Lin, F. F. Chen, Toppan Chunghwa Electronics Corp. (Taiwan)

7379 0Y **Multi-core advantages for mask data preparation** [7379-33]
J. Yeap, J. Nogatch, Synopsys, Inc. (United States)

7379 0Z **GPU-accelerated inverse lithography technique** [7379-34]
J. Zhang, Y. Deng, W. Xiong, Y. Peng, Z. Yu, Tsinghua Univ. (China)

7379 10 **Effect of scanner illumination and lens transmittance signatures on OPC accuracy** [7379-35]
H.-T Huang, A. Sezginer, Cadence Design Systems, Inc. (United States); J. K. Tyminski, Nikon Precision Inc. (United States)

7379 11 **Lithography compliance check considering neighboring cell structures for robust cell design** [7379-36]
M. Miyairi, S. Nojima, S. Maeda, K. Kodera, R. Ogawa, S. Tanaka, Toshiba Corp., Semiconductor Co. (Japan)

METROLOGY

7379 12 **The imaging performance of flash memory masks characterized with AIMS (Invited Paper)** [7379-37]
E. van Setten, O. Wismans, K. Grim, J. Finders, ASML Netherlands B.V. (Netherlands); M. Dusa, ASML TDC (United States); R. Birkner, R. Richter, T. Scherübl, Carl Zeiss SMS GmbH (Germany)

7379 13 **A new optical measurement method for verifying the exact change of thin films on the QZ blanks with ellipsometer** [7379-73]
S. Moon, S.-Y. Kim, G.-Y. Bang, B.-G. Kim, S.-G. Woo, H. Cho, SAMSUNG Electronics Co., Ltd. (Korea, Republic of)

7379 14 **Calibration strategies for precision stages in state-of-the-art registration metrology** [7379-39]
A. Huebel, U. Schellhorn, M. Arnz, G. Klose, Carl Zeiss SMT AG (Germany); D. Beyer, Carl Zeiss SMS GmbH (Germany)

7379 15 **In-die mask registration metrology for 32nm node DPT lithography** [7379-40]
K.-D. Roeth, F. Laske, M. Heiden, D. Adam, A. Boesser, KLA-Tencor GmbH (Germany); K. Rinn, A. Schepp, Univ. of Applied Sciences Giessen-Friedberg (Germany); J. Bender, KLA-Tencor GmbH (Germany)

7379 16 **Phase behavior through pitch and duty cycle and its impact on process window** [7379-41]
U. Buttgereit, R. Birkner, D. Seidel, S. Perlitz, Carl Zeiss SMS GmbH (Germany); V. Philipsen, P. De Bisschop, IMEC (Belgium)

WRITING TECHNOLOGY

7379 17 **E-beam shot count estimation at 32 nm HP and beyond** [7379-42]
J. Choi, S. H. Lee, D. Nam, B. G. Kim, S.-G. Woo, H. K. Cho, SAMSUNG Electronics Co., Ltd. (Korea, Republic of)

7379 18 **Present status of multi-column cell exposure system for mask writing** [7379-43]
H. Yasuda, A. Yamada, M. Yamabe, Association of Super-Advanced Electronics Technologies (Japan)

7379 19 **Mask and wafer evaluation of Sigma7500 pattern generator applied to 65nm logic metal and via layers** [7379-44]
F. Liu, I. Shi, Q. Liu, L. Zhu, S. Zhao, E. Guo, Semiconductor Manufacturing International Corp. (China)

7379 1A **Reduction of resist charging effect by EB reticle writer EBM-7000** [7379-45]
M. Saito, K. Ugajin, O. Ikenaga, Toshiba Corp. (Japan)

INSPECTION AND REPAIR I

7379 1B **Mask-LMC: lithographic simulation and defect detection from high-resolution mask images** [7379-46]
G. Chen, J. N. Wiley, J.-S. Wang, R. C. Howell, S. Bai, Y.-F. Chen, F. Chen, Y. Cao, Brion Technologies, Inc. (United States); T. Takigawa, T. Kurosawa, Brion Technologies KK (Japan); H. Tsuchiya, K. Usuda, M. Tokita, NuFlare Technology, Inc. (Japan); F. Ozaki, N. Kikuiri, Y. Tsuji, Advanced Mask Inspection Technology, Inc. (Japan)

7379 1C **Implementation strategy of wafer-plane and aerial-plane inspection for advanced mask manufacture** [7379-47]
W.-S. Kim, D.-H. Chung, C.-U. Jeon, H. Cho, Samsung Electronics, Co. Ltd. (Korea, Republic of); W. Huang, J. Miller, G. Inderhees, B. Pinto, KLA-Tencor Corp. (United States); J. Hur, K. Park, J. Han, KLA-Tencor Korea (Korea, Republic of)

7379 1D **Reticle inspection-based critical dimension uniformity** [7379-77]
V. Vellanki, C. Hess, G. Pan, C. Chen, G. Inderhees, D. Lopez, KLA-Tencor Corp. (United States)

7379 1F **Mask defect auto disposition based on aerial image in mask production** [7379-50]
C. Y. Chen, L. Tuo, C. S. Yoo, Tawian Seminconductor Manufacturing Company (Taiwan); L. Pang, D. Peng, J. Sun, Luminescent Technologies, Inc. (United States)

INSPECTION AND REPAIR II

7379 1G **Airborne molecular contamination detection method for photomasks and ultra purging decontamination** [7379-51]
H. Kambara, A. Favre, M. Davenet, Adixen by Alcatel-Lucent Co. (France); D. Rodier, Particle Measuring Systems, Inc. (United States)

7379 1H **A new approach to reticle haze defect management in the fab** [7379-52]
Y.-D. Gau, K. Hsiao, W.-H. Hsu, Y.-M. Lu, Nanya Technology Corp. (Taiwan); C.-C. Chen, C. M. Liu, M. Van Riet, N. Gaspar, C.-C. Yu, P. Chan, KLA-Tencor Corp. (United States)

7379 1I **Advances in post AFM repair cleaning of photomask with CO_2 cryogenic aerosol technology** [7379-53]
C. Bowers, I. Varghese, M. Balooch, W. Brandt, Eco-Snow Systems LLC, Linde AG (United States)

7379 1J **Selective removal of persistent particles with no photomask damage** [7379-54]
T. Robinson, R. Bozak, R. White, M. Archuletta, D. Lee, RAVE, LLC (United States)

MASK-RELATED LITHOGRAPHY

7379 1L **Comparison of lithographic performance between MoSi binary mask and MoSi attenuated PSM** [7379-56]
M. Yamana, Toppan Printing Co., Ltd. (Japan); M. Lamantia, Toppan Photomasks, Inc. (United States); V. Philipsen, IMEC (Belgium); S. Wada, T. Nagatomo, Y. Tonooka, Toppan Printing Co., Ltd. (Japan)

7379 1M **Trade-off between inverse lithography mask complexity and lithographic performance** [7379-57]
B.-G. Kim, S. S. Suh, B. S. Kim, S.-G. Woo, H. K. Cho, SAMSUNG Electronics Co., Ltd. (Korea, Republic of); V. Tolani, G. Dai, D. Irby, K. Wang, G. Xiao, D. Kim, K.-H. Baik, B. Gleason, Luminescent Technologies, Inc. (United States)

7379 1N **Double patterning addressing imaging challenges for near- and sub-k_1=0.25 node layouts** [7379-58]
B. –S. Seo, D.-K. Kang, M.-S. Noh, S.-H. Lee, SAMSUNG Electronics Co., Ltd. (Korea, Republic of); C. Cork, Synopsys SARL (France); G. LukPat, A. Miloslavsky, X. Li, K. Lucas, Synopsys, Inc. (United States); S. Lee, Synopsys Korea Inc. (Korea, Republic of)

7379 1O **Novel OPC and DfM methodology for 3D memory device** [7379-59]
T. Taguchi, T. Kotani, H. Mukai, H. Mashita, K. Iyanagi, K. Hashimoto, S. Inoue, Toshiba Corp., Semiconductor Co. (Japan)

7379 1P **High sensitivity electric field monitoring system for control of field-induced CD degradation in reticles (EFM)** [7379-60]
T. Sebald, ESTION GmbH & Co. KG (Germany); G. Rider, Microtome, Inc. (United States)

POSTER SESSION: MATERIAL AND PROCESS

7379 1Q **The art of photomask materials for low-k1-193nm lithography** [7379-114]
M. Hashimoto, H. Iwashita, H. Mitsui, HOYA Corp. (Japan)

7379 1R **Evaluation of the flatness effects of mask backing and orientation during photomask pellicle mount** [7379-61]
T. Mizoguchi, S. Akutagawa, Toppan Photomasks, Inc. (United States); M. Barrett, M. Caterer, R. Nolan, K. Racette, D. Plouffe, N. Zhou, IBM Corp. (United States)

7379 1S **Evaluation for EAPSM life time by ArF pellicle characteristic** [7379-62]
K. J. Seo, J. S. Ryu, G. M. Jeong, S. C. Kang, Y. D. Kim, S. C. Kim, C. Y. Kim, Hynix Semiconductor Inc. (Korea, Republic of)

7379 1T **In situ selectivity monitor for dry etch of photomasks** [7379-63]
T. Zhou, J. Chen, M. Grimbergen, M. Chandrachood, I. Ibrahim, A. Kumar, Applied Materials, Inc. (United States)

7379 1U **Plasma optical emission analysis for chamber condition monitor** [7379-64]
Z. Mao, T. Zhou, M. Grimbergen, D. Bivens, D. Knick, R. Koch, M. Chandrachood, J. Chen, I. Ibrahim, A. Kumar, Applied Materials, Inc. (United States)

7379 1V **Fine pattern fabrication property of binary mask and attenuated phase shift mask** [7379-65]
T. Yamazaki, Y. Kojima, M. Yamana, T. Haraguchi, T. Tanaka, Toppan Printing Co., Ltd. (Japan)

7379 1W **Applied analytics on EAPSM Cr plasma etch optimization utilizing design of experiment** [7379-67]
M. J. Tian, E. Wang, Z. H. Zhu, Semiconductor Manufacturing International Corp. (China)

7379 1X **Study of electric-field-induced-development method** [7379-68]
M. Terayama, H. Sakurai, M. Sakai, M. Itoh, O. Ikenaga, Toshiba Corp. (Japan); H. Funakoshi, Tokyo Electron Kyushu Ltd. (Japan); T. Shiozawa, S. Miyazaki, Y. Saito, Tokyo Electron Ltd. (Japan); N. Hayashi, Dai Nippon Printing Co., Ltd. (Japan)

7379 1Y **Two-fluid cleaning technology for advanced photomask** [7379-115]
T. Kikuchi, N. Kobayashi, Y. Kurokawa, H. Hirose, M. Nonaka, Shibaura Mechatronics Corp. (Japan)

SESSION 16 POSTER SESSION: WRITING TECHNOLOGY

7379 1Z **Improvement of data transfer speed and development of an EB data verification system in a VSB mask writer** [7379-70]
O. Wakimoto, H. Manabe, H. Hoshi, N. Samoto, JEOL Ltd. (Japan) and Association of Super-Advanced Electronic Technologies (Japan; T. Komagata, Y. Nakagawa, JEOL Ltd. (Japan); M. Yamabe, Association of Super-Advanced Electronics Technologies (Japan)

7379 21 **Quantification of electron-beam proximity effects using a virtual direct write environment** [7379-72]
M. Schulz, Synopsys GmbH (Germany); P. Brooker, A. Zepka, G. Meyers, Synopsys, Inc. (United States)

POSTER SESSION: METROLOGY

7379 22 **An evaluation of a new side-wall-angle measurement technique for mask patterns by CD-SEM** [7379-38]
H. Hakii, I. Yonekura, M. Kawashita, Y. Kojima, Y. Sakamoto, K. Tanaka, Toppan Printing Co., Ltd. (Japan)

7379 24 **CD performance evaluation according to advanced marking parameter** [7379-75]
S.-K. Yoon, S.-Y. Kim, K.-M. Yeon, C. Lim, S.-J. Choi, J.-H. Kim, L.-J. Kim, Y.-R. Cho, H.-S. Kim, Toppan Photomasks Korea, Ltd. (Korea, Republic of)

7379 25 **Phase-shift/transmittance measurements in a micro pattern using MPM193EX** [7379-76]
H. Nozawa, T. Ishida, S. Kato, O. Sato, K. Miyazaki, K. Takehisa, N. Awamura, H. Takizawa, H. Kusunose, Lasertec Corp. (Japan)

POSTER SESSION: INSPECTION TOOLS AND TECHNOLOGIES

7379 27 **An open-architecture approach to defect analysis software for mask inspection systems** [7379-79]
M. Pereira, R. R. Pai, M. M. Reddy, R. M. Krishna, SoftJin Technologies Pvt. Ltd. (India)

POSTER SESSION: REPAIRING TOOLS AND TECHNOLOGIES

7379 28 **The study of defect detection method for 32nm technology node and beyond** [7379-80]
K. Seki, M. Shibita, S. Akima, Toppan Printing Co., Ltd. (Japan)

7379 29 **Variable sensitivity detection (VSD) technology for screening SRAF nuisance defects** [7379-81]
K. Yamashita, N. Harabe, M. Hirono, Y. Tamura, I. Isomura, Y. Tsuji, Advanced Mask Inspection Technology, Inc. (Japan); E. Matsumoto, NuFlare Technology, Inc. (Japan)

7379 2A **A study of mask inspection method with pattern priority and printability check** [7379-82]
M. Tokita, H. Tsuchiya, T. Inoue, T. Inoue, M. Yamabe, Association of Super-Advanced Electronics Technologies (Japan)

7379 2B **TeraScanXR: a high sensitivity and throughput photomask inspection system** [7379-83]
B. Mu, A. Dayal, A. Goonesekera, P. Lim, C. Chen, P. Liu, K. Yeung, B. Pinto, B. Broadbent, G. Inderhees, KLA-Tencor Corp. (United States)

7379 2C **A noble evaluation method for repaired area utilizing SEM images** [7379-84]
K. Morishita, S. Kanamitsu, T. Hirano, Toshiba Corp., Semiconductor Co. (Japan)

7379 2D **Semi-automated repair verification of aerial images** [7379-85]
E. Poortinga, Carl Zeiss SMT Inc. (United States); T. Schereubl, R. Richter, Carl Zeiss SMS GmbH (Germany)

POSTER SESSION: EUVL MASK

7379 2G **Novel absorber materials for EUV lithography mask** [7379-88]
T. Matsuo, K. Kanayama, Y. Okumoto, Toppan Printing Co., Ltd. (Japan)

7379 2H **The impact of mask design on EUV imaging** [7379-89]
T. Schmoeller, Synopsys GmbH (Germany); J. K. Tyminski, Nikon Precision Inc. (United States); J. Lewellen, Synopsys Inc. (United States); W. Demmerle, Synopsys GmbH (Germany)

7379 2I **Study of CD variation at EUV mask fabrication occurred by electric conduction from top to back side** [7379-90]
K. Takai, K. Murano, K. Hagihara, M. Itoh, Toshiba Corp. (Japan); T. Abe, T. Adachi, H. Akizuki, T. Takikawa, H. Mohri, N. Hayashi, Dai Nippon Printing Co., Ltd. (Japan)

7379 2J **Actinic mask inspection using an extreme ultraviolet microscope** [7379-91]
K. Takase, Y. Kamaji, T. Iguchi, Univ. of Hyogo (Japan); T. Sugiyama, T. Uno, Asahi Glass Co., Ltd. (Japan); T. Harada, T. Watanabe, H. Kinoshita, Univ. of Hyogo (Japan)

7379 2K **Evaluation of EUVL mask pattern defect inspection using 199nm inspection tool with super-resolution method** [7379-92]
H. Shigemura, T. Amano, Y. Nishiyama, O. Suga, Y. Arisawa, MIRAI Semiconductor Leading Edge Technologies, Inc. (Japan); H. Hashimoto, K. Takahara, K. Usuda, NuFlare Technology, Inc. (Japan); N. Kikuiri, R. Hirano, Advanced Mask Inspection Technology, Inc. (Japan)

7379 2L **FIB mask repair technology for EUV mask** [7379-93]
T. Amano, Y. Nishiyama, H. Shigemura, T. Terasawa, O. Suga, MIRAI Semiconductor Leading Edge Technologies, Inc. (Japan); K. Shiina, F. Aramaki, A. Yasaka, SII NanoTechnology Inc. (Japan); T. Abe, H. Mohri, Dai Nippon Printing Co., Ltd. (Japan)

7379 2O **Go proton: investigation on mask patterning for the 22nm hp node using a ML2 multibeam system** [7379-96]
J. Butschke, M. Irmscher, H. Sailer, Institut für Mikroelektronik Stuttgart Chips (Germany); H. Loeschner, E. Platzgummer, Institut für Mikroelektronik Stuttgart Nanofabrication AG (Austria)

POSTER SESSION: NIL AND PATTERNING MEDIA

7379 2Q **Developing quartz wafer mold manufacturing process for patterned media** [7379-98]
T. Chiba, M. Fukuda, M. Ishikawa, K. Itoh, M. Kurihara, M. Hoga, Dai Nippon Printing Co., Ltd. (Japan)

7379 2S **Progress of UV-NIL template making** [7379-100]
T. Hiraka, J. Mizuochi, Y. Nakanishi, S. Yusa, S. Sasaki, Y. Morikawa, H. Mohri, N. Hayashi, Dai Nippon Printing Co., Ltd. (Japan)

POSTER SESSION: MASK-RELATED LITHOGRAPHY

7379 2T **Model-based assist feature insertion for sub-40nm memory device** [7379-101]
S. Suh, S. Lee, S. Choi, S.-W. Lee, C. Park, SAMSUNG Electronics Co., Ltd. (Korea, Republic of)

POSTER SESSION: EDA, DFM, AND MDP

7379 2Y **Optimizing computing resources for optimal throughput in a mask data preparation flow** [7379-107]
W. Zhang, R. Bennett, P. Ghosh, S. Schulze, A. Bowhill, Mentor Graphics Corp. (United States)

7379 2Z **Model-based assist features** [7379-108]
B. Yenikaya, O. Alexandrov, S. Chen, A. Liu, A. Mokhberi, A. Sezginer, Cadence Design Systems, Inc. (United States)

7379 30 **Improvement of simulation accuracy using a non Gaussian kernel** [7379-116]
H. Futatsuya, T. Yamamoto, Fujitsu Microelectronics Ltd. (Japan); S. Yoshikawa, Fujitsu VLSI Ltd. (Japan); T. Chijimatsu, S. Asai, Fujitsu Microelectronics Ltd. (Japan)

7379 31 **Evaluation of mask data format standard OASIS.MASK developed for mask tools** [7379-109]
T. Suzuki, Dai Nippon Printing Co., Ltd. (Japan); Y. Nagaoka, Y. Maenaka, KLA-Tencor Corp. (United States); V. Vellanki, W. Ruch, KLA-Tencor Japan Ltd. (Japan); M. Mori, K. Hattori, K. Hosono, Renesas Technology Corp. (Japan); S. Narukawa, M. Hoga, H. Mohri, Dai Nippon Printing Co., Ltd. (Japan)

7379 32 **Utilization of design intent information for mask manufacturing (II)** [7379-110]
K. Kato, M. Endo, T. Inoue, M. Yamabe, Association of Super-Advanced Electronics Technologies (Japan)

7379 33 **Study of the pattern categorization method in verification of OPC pattern** [7379-111]
M. Naoe, T. Miyauchi, Fujitsu VLSI Ltd. (Japan); S. Makino, K. Suzuki, M. Oseki, T. Okada, Fujitsu Microelectronics Ltd. (Japan)

POSTER SESSION: STRATEGY AND BUSINESS

7379 34 **Organized DFM** [7379-112]
T. Sato, Toshiba Corp. (Japan); M. Honma, NEC Electronics Corp. (Japan); H. Itoh, Sharp Corp. (Japan); N. Iriki, Renesas Technology Corp. (Japan); S. Kobayashi, Toshiba Corp. (Japan); N. Miyazaki, Fujitsu Microelectronics Ltd. (Japan); T. Onodera, Oki Semiconductor Co., Ltd. (Japan); H. Suzuki, SANYO Semiconductor Co., Ltd. (Japan); N. Yoshioka, Fujitsu Microelectronics Ltd. (Japan); S. Arima, Univ. of Tsukuba (Japan); K. Kadota, National Institute of Advanced Industrial Science and Technology (Japan)

7379 35 **Automated reticle inspection data analysis for wafer fabs** [7379-113]
D. Summers, G. Chen, Freescale Semiconductor, Inc. (United States); B. Reese, T. Hutchinson, M. Liesching, H. Ying, R. Dover, KLA-Tencor Corp. (United States)

Author Index

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